# Quad 2-Input NAND Schmitt Trigger

The MC74LVX132 is an advanced high speed CMOS Schmitt NAND trigger fabricated with silicon gate CMOS technology.

Pin configuration and function are the same as the MC74LVX00, but the inputs have hysteresis.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0~V, allowing the interface of 5.0~V systems to 3.0~V systems.

## **Features**

- High Speed:  $t_{PD} = 5.8 \text{ ns}$  (Typ) at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu A$  (Max) at  $T_A = 25$ °C
- Power Down Protection Provided on Inputs
- Low Noise:  $V_{OLP} = 0.5 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V;

Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant

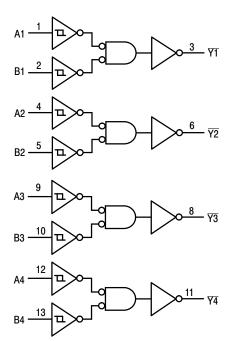


Figure 1. Logic Diagram

# **FUNCTION TABLE**

A Input	B Input	▼ Output
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L



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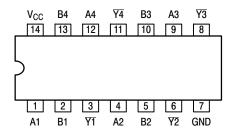
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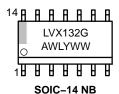
SOIC-14 NB D SUFFIX CASE 751A TSSOP-14 DT SUFFIX CASE 948G

#### **PIN ASSIGNMENT**



14-Lead (Top View)

#### **MARKING DIAGRAMS**





TSSOP-14

LVX132 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

## MC74LVX132

#### **MAXIMUM RATINGS**

Symbol	Pa	arameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		$-0.5$ to $V_{CC} + 0.5$	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>I</sub> < GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current	V <sub>O</sub> < GND	±20	mA
l <sub>OUT</sub>	DC Output Sink Current		±25	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±50	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for	10 Seconds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
$\theta_{JA}$	Thermal Resistance	SOIC TSSOP	250	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C	SOIC TSSOP	250	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL 94-V0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 N/A	V
I <sub>Latchup</sub>	Latchup Performance	Above V <sub>CC</sub> and Below GND at 85°C (Note 4)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Tested to EIA/JESD22-A114-A.
- Tested to EIA/JESD22-A115-A.
   Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Supply Voltage	2.0	3.6	V
VI	Input Voltage (Note 5)	0	5.5	V
Vo	Output Voltage (HIGH or LOW State)	0	5.5	V
T <sub>A</sub>	Operating Free–Air Temperature	-40	+ 125	°C
Δt/ΔV	Input Transition Rise or Fall Rate $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

# **MC74LVX132**

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	٦	Γ <sub>A</sub> = 25°C	<b>C</b>	<b>T</b> <sub>A</sub> = ≤	€ 85°C	<b>T</b> <sub>A</sub> = ≤	125°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>T+</sub>	Positive Threshold Voltage (Figure 4)		2.0 3.0 3.6	1.15 1.50 1.70	1.31 1.82 2.12	1.60 2.25 2.60	1.15 1.50 1.70	1.60 2.25 2.60	1.15 1.50 1.70	1.60 2.25 2.60	V
V <sub>T-</sub>	Negative Threshold Voltage (Figure 4)		2.0 3.0 3.6	0.30 0.75 1.00	0.64 1.13 1.46	0.9 1.45 1.90	0.30 0.75 1.00	0.90 1.45 1.90	0.30 0.75 1.00	0.90 1.45 1.90	V
V <sub>H</sub>	Hysteresis Voltage (Figure 4)		2.0 3.0 3.6	0.30 0.30 0.35	0.70 0.76 0.69	1.30 1.50 1.60	0.30 0.30 0.35	1.30 1.50 1.60	0.30 0.30 0.35	1.30 1.50 1.60	V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 mA$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		1.9 2.9 2.34		V
V <sub>OL</sub>	Maximum Low–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50 μA I <sub>OL</sub> = 50 μA I <sub>OL</sub> = 4 mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44		0.1 0.1 0.52	V
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	3.6			±0.1		±1.0		±1.0	μΑ
Icc	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			2.0		20		20	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

				T <sub>A</sub> = 25°C		T <sub>A</sub> = ≤ 85°C		T <sub>A</sub> = ≤ 125°C			
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay,	V <sub>CC</sub> = 2.7V	$C_L = 15pF$ $C_L = 50pF$		7.0 10.0	11.0 16.0	1.0 1.0	13.0 18.7	1.0 1.0	15.0 20.0	ns
	A or B to $\overline{Y}$	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		5.8 8.3	10.6 15.4	1.0 1.0	12.5 17.5	1.0 1.0	14.5 19.5	
t <sub>OSHL</sub> ,	Output to Output Skew	V <sub>CC</sub> = 2.7V	C <sub>L</sub> = 50pF			1.5		1.5		1.5	ns
toslh	(Note 6)	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 50pF			1.5		1.5		1.5	
C <sub>in</sub>	Maximum Input Capacitance				4	10		10		10	pF
				Typical @ 25°C, V <sub>CC</sub> = 5.0 V							
C <sub>PD</sub>	Power Dissipation Capacit	tance (Note 6)					11				pF

<sup>6.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/4 (per gate). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.5	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.5	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

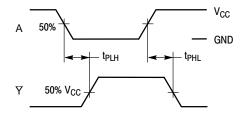
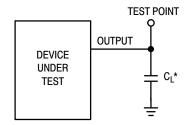


Figure 2. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 3. Test Circuit

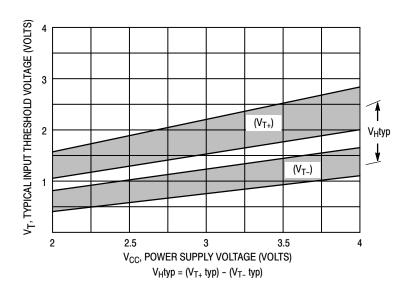
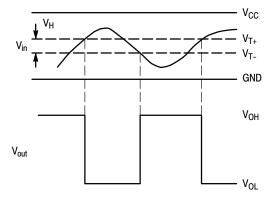
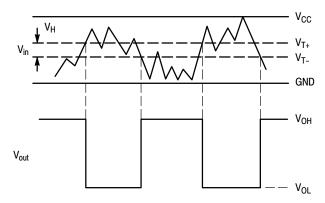


Figure 4. Typical Input Threshold,  $V_{T+}$ ,  $V_{T-}$  versus Power Supply Voltage

# MC74LVX132





- (a) A Schmitt-Trigger Squares Up Inputs With Slow Rise and Fall Times
- (b) A Schmitt-Trigger Offers Maximum Noise Immunity

Figure 5. Typical Schmitt-Trigger Applications

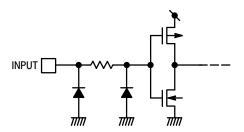


Figure 6. Input Equivalent Circuit

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LVX132DR2G	SOIC-14 NB (Pb-Free)	2500 Tape & Reel
MC74LVX132DTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74LVX132DTR2G	TSSOP-14 (Pb-Free)	2500 Tape & Reel

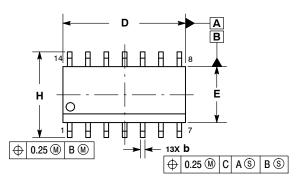
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

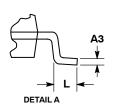


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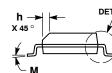
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 





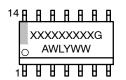




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
  - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIM	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.35	1.75	0.054	0.068	
A1	0.10	0.25	0.004	0.010	
АЗ	0.19	0.25	0.008	0.010	
b	0.35	0.49	0.014	0.019	
D	8.55	8.75	0.337	0.344	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.019	
L	0.40	1.25	0.016	0.049	
M	0 °	7°	0 °	7°	

# **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

# **SOLDERING FOOTPRINT\***

1	6.50 –	<b>-</b>	14X 1.18
			_ 1.27
_			PITCH
14X 1			_
14X 10.58			

**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **STYLES ON PAGE 2**

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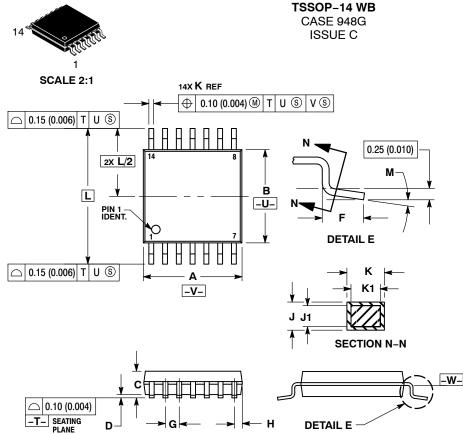
# SOIC-14 CASE 751A-03 ISSUE L

# DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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**DATE 17 FEB 2016** 

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

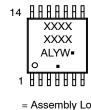
  3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY.
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0°	8 °	0 °	8 °

# **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot ٧ = Year

W = Work Week

= Pb-Free Package (Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

SOLDERING FOOTPRINT					
7.	06				
1					
<del></del>					
J	————   PITCH				
14X 0.36	<del></del>				
0.36 → 1.26	DIMENSIONS: MILLIMETERS				

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